

Transistor Circuit With Varying Resistance Lightly Doped Diffused Regions
For Electrostatic Discharge ("ESD") Protection

ABSTRACT OF THE DISCLOSURE

A method of forming a transistor (70) in a semiconductor active area (78). The method forms a gate structure (G_2) in a fixed relationship to the semiconductor active area thereby defining a first source/drain region (R_1) adjacent a first gate structure sidewall and
5 a second source/drain region (R_2) adjacent a second sidewall gate structure. The method also forms a lightly doped diffused region (80_1) formed in the first source/drain region and extending under the gate structure, wherein the lightly doped diffused region comprises a varying resistance in a direction parallel to the gate structure.